	Code No.: 13406	0
V	ASAVI COLLEGE OF ENGINEERING (Autonomous), HYDERABAD B.E. (ECE) II Year I-Semester Backlog Examinations, December-2017	
	Electronic Materials & Devices	
Tim	me: 3 hours Max. Marks: 70	
	Note: Answer ALL questions in Part-A and any FIVE from Part-B	
	$Part-A (10 \times 2 = 20 Marks)$	
1.	The reverse saturation current of a silicon PN junction diode is $10\mu A$. Calculate the diode current for forward bias voltage of $0.6V$ at $25^{\circ}C$.	
2.	Distinguish between a PN junction and a schottky junction.	
3.	Define Ripple factor and PIV.	
4.	State the principle of operation of a Light Emitting Diode.	
5.	Determine I_E and α for a transistor circuit having I_B =15 μ A and β =150.	
6.	What is early effect in a BJT?	
7.	Write a short comparison of CE,CC and CB configurations.	
8.	What is holding and latching current of SCR?	
9.	Prove that the Transconductance $g_m = -(2/V_p)(I_D.I_{DSS})^{1/2}$.	
10.	Compare enhancement and depletion MOSFET.	
	Part-B $(5 \times 10 = 50 \text{ Marks})$	
11.	a) Derive an expression for transition capacitance of a diode.	
	b) Draw and explain the V-I characteristics of Zener diode.	[
12.	a) Analyze the bridge rectifier for its ripple factor, efficiency and PIV.	[
	b) Explain the working principle of photo diode and list its applications.	[
13.	a) Draw and explain the output characteristics of BJT in CE configuration. What are the three regions of operation? How can they be demarcated in the output characteristics?	

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b) What is thermal runaway and how can it be prevented?

14. a) Analyze Emitter follower circuit for its current gain and voltage gain.

b) Write a short note on Varactor diode and state its applications.

17. Answer any two of the following:

a) Thermal stabilization of BJT.

c) Compare BJT with FET.

b) Write short notes on DIAC and TRIAC.

b) Draw and explain the working of a UJT with the help of its characteristics.

b) Draw and explain the construction and operation of an enhancement MOSFET.

16. a) Write a short note on PN junction formation techniques and list diode applications.

15. a) Draw the structure of JFET and explain the drain and transfer characteristics.